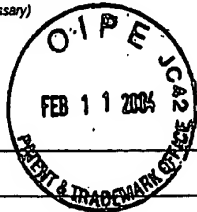


Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known Application Number 09/945535 Filing Date August 30, 2001 First Named Inventor Ahn, Kie Group Art Unit 2813 Examiner Name Blum, David	
Sheet 1 of 1		Attorney Docket No: 1303.026US1	



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Examiner Initials *	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AS		CHAMBERS, J J., et al., "Physical and electrical characterization of ultrathin yttrium silicate insulators on silicon", <u>Journal of Applied Physics</u> , 90(2), (July 15, 2001), 918-33	
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[Signature]

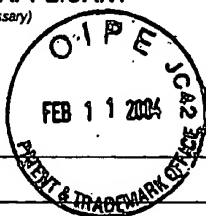
DATE CONSIDERED

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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

**Complete if Known**

Application Number	09/945535
Filing Date	August 30, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David

Sheet 1 of 1

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		KUKLI, KAUPPO, et al., "Low-Temperature Deposition of Zirconium Oxide-Based Nanocrystalline Films by Alternate Supply of Zr[OC(CH ₃) ₃] ₄ and H ₂ O", <u>Chemical Vapor Deposition</u> , 6(6), (2000), 297-302	
		NAKAJIMA, ANRI, "Soft breakdown free atomic-layer-deposited silicon-nitride/SiO ₂ /sub 2/ stack gate dielectrics", <u>International Electron Devices Meeting. Technical Digest</u> , (2001), 6.5.1-4	
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		WOLF, S., et al., In: <u>Silicon Processing of the VLSI Era</u> , Vol. 1, Lattice Press, 374-380	

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Substitute Disclosure Statement Form (PTO-1449)

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